

REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 29-48 are pending in the present application. The abstract and Claims 29, 30 and 32 are amended by the present amendment. Claims 1-28 were previously canceled without prejudice or disclaimer. Support for this Amendment can be found at least on page 9, lines 10-21, page 11, line 26 to page 12, line 1, and page 16, lines 12-18.

In the outstanding Office Action, the IDS was objected to; the specification was objected to; Claims 29-31 were rejected under 35 U.S.C. § 102(b) as anticipated by U.S. Patent No. 5,740,099 to Tanigawa; Claims 32-34 were indicated as be allowable if rewritten in independent form; and Claims 35-38 were allowed.

Applicants thank the Examiner for the indication of allowable subject matter. In light of this indication, Claim 32 has been rewritten in independent form. Accordingly, Applicants respectfully request that the objection to independent Claim 32 and Claims 33-34 depending therefrom be withdrawn.

Applicants note acknowledgement of the IDS, filed on April 21, 2004, has not been fully acknowledged. Copies of the Foreign Patent Documents and the Non Patent Literature Documents listed on the PTO Form 1449 were previously cited in parent application 09/995,594, filed on November 29, 2001. Accordingly, it is respectfully requested that an initialed copy of the PTO form 1449, with the IDS filed on April 21, 2004, be issued.

In response to the objection to the abstract, the abstract has been amended to address informalities as suggested by the Examiner. Accordingly, Applicants respectfully request that the objection to the abstract be withdrawn.

Applicants respectfully traverse the rejection of Claims 29-31 under 35 U.S.C. § 102(b) as anticipated by Tanigawa.

Amended Claim 29 is directed to a semiconductor chip comprising, *inter alia*, **a single crystal layer epitaxially grown on a part of the base substrate** having a first device-fabrication surface in which a bulk device is positioned.

Tanigawa describes a semiconductor dynamic random access memory device that is fabricated on a semiconductor substrate. As shown in Figure 4, p-type wells 30f and n-type wells 30g are formed in the bulk region 30b by diffusion of the ion-implanted boron and the ion-implanted phosphorous in the p-type semiconductor substrate 30.¹ Tanigawa does not disclose or suggest an epitaxially grown single crystal layer.

Therefore, Tanigawa does not disclose or suggest **a single crystal layer epitaxially grown on a part of the base substrate** having a first device fabrication surface in which a bulk device is positioned.

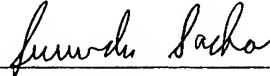
Accordingly, Applicants respectfully request that the objection with respect to amended independent Claim 29 and Claims 30-31 depending therefrom be withdrawn.

¹ Tanigawa at Fig. 4, Column 6, lines 23-25 and Column 8, lines 63-67.

Consequently, in light of the above discussion and in view of the present amendment, the present application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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